# Low-Voltage CMOS Octal Transceiver

# With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX245 is a high performance, non–inverting octal transceiver operating from a 2.0 to 5.5 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V $_{\rm I}$  specification of 5.5 V allows MC74LCX245 inputs to be safely driven from 5 V devices if V $_{\rm CC}$  is less than 5.0 V. The MC74LCX245 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at both A and B ports. The Transmit/Receive  $(T/\overline{R})$  input determines the direction of data flow through the bi–directional transceiver. Transmit (active–HIGH) enables data from A ports to B ports; Receive (active–LOW) enables data from B to A ports. The Output Enable input, when HIGH, disables both A and B ports by placing them in a HIGH Z condition.

#### **Features**

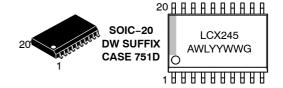
- Designed for 2.0 to 5.5 V V<sub>CC</sub> Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- $I_{OFF}$  Specification Guarantees High Impedance When  $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
   Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V Machine Model >200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



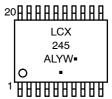
# ON Semiconductor®

http://onsemi.com

#### MARKING DIAGRAMS

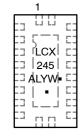








QFN20 MN SUFFIX CASE 485AA



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

1

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

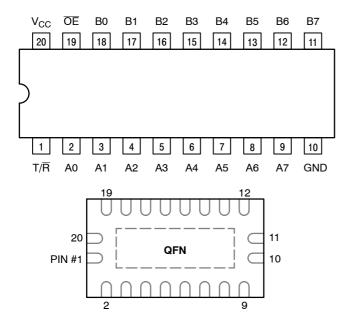


Figure 1. Pinout (Top View)

## **PIN NAMES**

FUNCTION
Output Enable Input
Transmit/Receive Input
Side A 3-State Inputs or 3-State Outputs
Side B 3-State Inputs or 3-StateOutputs

#### **TRUTH TABLE**

INF	PUTS	OPERATING MODE		
ŌĒ	T/R	Non-Inverting		
L	L	B Data to A Bus		
L	Н	A Data to B Bus		
Н	X	Z		

H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State

X = High or Low Voltage Level and Transitions are Acceptable

For I<sub>CC</sub> reasons, Do Not Float Inputs

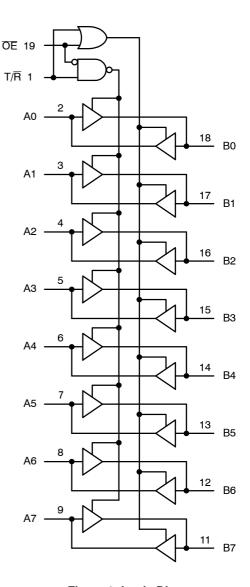


Figure 2. Logic Diagram

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	DC Supply Voltage	−0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_0 \le +7.0$	Output in 3-State	٧
		$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	٧
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
		+50	V <sub>O</sub> > V <sub>CC</sub>	mA
Io	DC Output Source/Sink Current	±50		mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I<sub>O</sub> absolute maximum rating must be observed.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Тур	Max	Unit
V <sub>CC</sub>	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	5.5 5.5	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage	(HIGH or LOW State) (3-State)	0		V <sub>CC</sub> 5.5	V
I <sub>OH</sub>	HIGH Level Output Current	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			- 24 - 12 - 8	mA
I <sub>OL</sub>	LOW Level Output Current	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+ 24 + 12 + 8	mA
T <sub>A</sub>	Operating Free-Air Temperature		-55		+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V <sub>IN</sub> from 0	0.8 V to 2.0 V, V <sub>CC</sub> = 3.0 V	0		10	ns/V

#### DC ELECTRICAL CHARACTERISTICS

			T <sub>A</sub> = −55°C	to +125°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V <sub>IH</sub>	HIGH Level Input Voltage (Note 2)	$2.3 \text{ V} \le \text{V}_{CC} \le 2.7 \text{ V}$	1.7		V
		$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}$	2.0		
V <sub>IL</sub>	LOW Level Input Voltage (Note 2)	$2.3 \text{ V} \le \text{V}_{CC} \le 2.7 \text{ V}$		0.7	V
		$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}$		0.8	
V <sub>OH</sub>	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ I}_{OL} = 100 \mu\text{A}$	V <sub>CC</sub> - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8		
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC}$ = 3.0 V; $I_{OH}$ = -24 mA	2.2		
V <sub>OL</sub>	LOW Level Output Voltage	2.3 V $\leq$ V $_{CC} \leq$ 3.6 V; I $_{OL}$ = 100 $\mu A$		0.2	V
		$V_{CC} = 2.3 \text{ V; } I_{OL} = 8 \text{ mA}$		0.6	
		$V_{CC} = 2.7 \text{ V}; I_{OL} = 12 \text{ mA}$		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 16 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 24 mA		0.55	
I <sub>OZ</sub>	3-State Output Current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$		±5	μΑ
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>CC</sub> = 0, V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V		10	μΑ
I <sub>IN</sub>	Input Leakage Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 5.5 V or GND		±5	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 5.5 V or GND		10	μΑ
$\Delta I_{CC}$	Increase in I <sub>CC</sub> per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

<sup>2.</sup> These values of V<sub>I</sub> are used to test DC electrical characteristics only.

## AC CHARACTERISTICS $t_R$ = $t_F$ = 2.5 ns; $R_L$ = 500 $\Omega$

				Limits							
				T <sub>A</sub> = -55°C to +125°C							
			V <sub>CC</sub> = 3.3	3 V ± 0.3V	V <sub>CC</sub> =	2.7 V	V <sub>CC</sub> = 2.5	V ± 0.2V	V <sub>CC</sub> =	5.0 V	
			C <sub>L</sub> =	50 pF	C <sub>L</sub> =	50 pF	C <sub>L</sub> = 3	30 pF	C <sub>L</sub> =	50 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Input to Output	1	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	1.5 1.5	8.4 8.4	1.5 1.5	5.0 5.0	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time to High and Low Level	2	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	1.5 1.5	10.5 10.5	1.5 1.5	7.0 7.0	ns
t <sub>PHZ</sub>	Output Disable Time From High and Low Level	2	1.5 1.5	7.5 7.5	1.5 1.5	8.5 8.5	1.5 1.5	9.0 9.0	1.5 1.5	6.0 6.0	ns
toshl toshh	Output-to-Output Skew (Note 3)			1.0 1.0		1.0 1.0		1.0 1.0		1.0 1.0	ns

<sup>3.</sup> Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

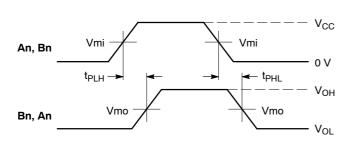
#### **DYNAMIC SWITCHING CHARACTERISTICS**

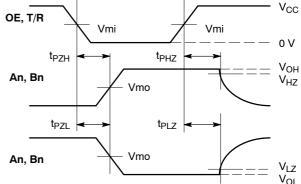
			T,	<sub>A</sub> = +25°	С	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>OLP</sub>	Dynamic LOW Peak Voltage (Note 4)	$V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V}$		0.8 0.6		V V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage (Note 4)	$V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V}$		-0.8 -0.6		V V

<sup>4.</sup> Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

## **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	7	pF
C <sub>I/O</sub>	Input/Output Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, $V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	25	pF



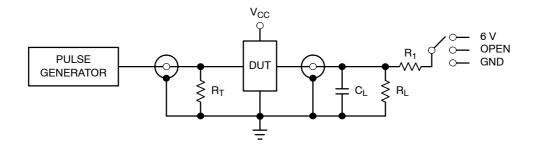


#### 

WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES  $t_{R}=t_{F}=2.5 \text{ ns},\ 10\% \text{ to } 90\%;\ f=1 \text{ MHz};\ t_{W}=500 \text{ ns}$ 

Figure 3. AC Waveforms

	V <sub>CC</sub>				
Symbol	3.3 V ± 0.3 V	2.7 V	2.5 V ± 0.2 V	5.0 V	
Vmi	1.5 V	1.5 V	V <sub>CC</sub> /2	V <sub>CC</sub> /2	
Vmo	1.5 V	1.5 V	V <sub>CC</sub> /2	V <sub>CC</sub> /2	
V <sub>HZ</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.15 V	V <sub>OL</sub> + 0.15 V	
V <sub>LZ</sub>	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.15 V	V <sub>OH</sub> – 0.15 V	



TEST	SWITCH
t <sub>PLH</sub> , t <sub>PHL</sub>	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	6 V at V <sub>CC</sub> = $3.3 \pm 0.3$ V 6 V at V <sub>CC</sub> = $2.5 \pm 0.2$ V
Open Collector/Drain t <sub>PLH</sub> and t <sub>PHL</sub>	6 V
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND

 $C_L$  = 50 pF at  $V_{CC}$  = 3.3  $\pm$ 0.3 V or equivalent (includes jig and probe capacitance)  $C_L$  = 30 pF at  $V_{CC}$  = 2.5  $\pm$ 0.2 V or equivalent (includes jig and probe capacitance)  $R_L$  =  $R_1$  = 500  $\Omega$  or equivalent

 $R_T = Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

Figure 4. Test Circuit

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LCX245DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LCX245DWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74LCX245DTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74LCX245DTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel
NLV74LCX245DTR2G*	TSSOP-20 (Pb-Free)	2500 Tape & Reel
MC74LCX245MNTWG	QFN20 (Pb–Free)	3000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.





QFN20, 2.5x4.5 MM CASE 485AA-01 UE B

**DATE 30 APR 2010** 

#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. DIMENSIONS & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.

  4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIN	MILLIMETERS					
DIM	MIN	MAX					
Α	0.80	1.00					
A1	0.00	0.05					
A3	0.20 REF						
b	0.20	0.30					
D	2.50	BSC					
D2	0.85	1.15					
Е	4.50	BSC					
E2	2.85	3.15					
е	0.50 BSC						
K	0.20						
L	0.35	0.45					

#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code

= Assembly Location Α

= Wafer Lot L Υ = Year W = Work Week

= Pb-Free Package (Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

C 121.	ISSU
20 SCALE 2:1	
	— D — A B
PIN ONE REFERENCE	E
2X  2X  2X  0.15 C	TOP VIEW
// 0.10 C C C COX C C C C C C C C C C C C C C C	(A3) A1 C SEATING PLANE
20X L 9	D2
0.10 C A B 2 C NOTE 3	1 20 K

DOCUMENT NUMBER:	98AON12653D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	QFN20. 2.5X4.5 MM		PAGE 1 OF 1	

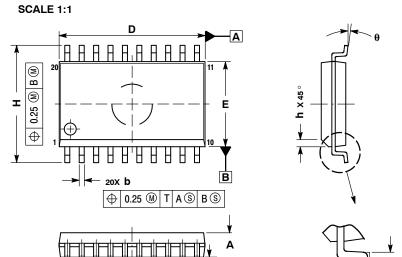
ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.





SOIC-20 WB CASE 751D-05 **ISSUE H** 

**DATE 22 APR 2015** 



- DIMENSIONS ARE IN MILLIMETERS.
   INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

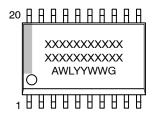
	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
b	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
A	0 °	7 °	

#### RECOMMENDED **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42343B	B42343B  Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-20 WB		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

0.100 (0.004) -T- SEATING

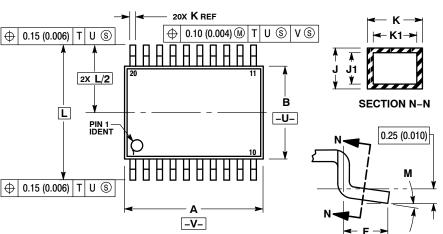
**SOLDERING FOOTPRINT** 

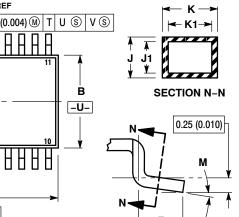
- 7.06

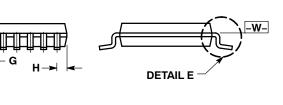


#### TSSOP-20 WB CASE 948E ISSUE D

**DATE 17 FEB 2016** 







**DETAIL E** 

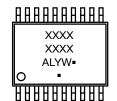
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	٥°	80	٥°	80

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASH70169A	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP-20 WB		PAGE 1 OF 1	

DIMENSIONS: MILLIMETERS

0.65

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

0.36

16X

1.26

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales